

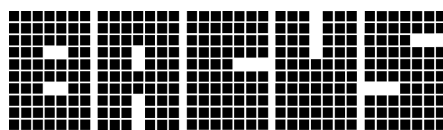
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Emily E. Gallagher
Jed H. Rankin
Editors

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